

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

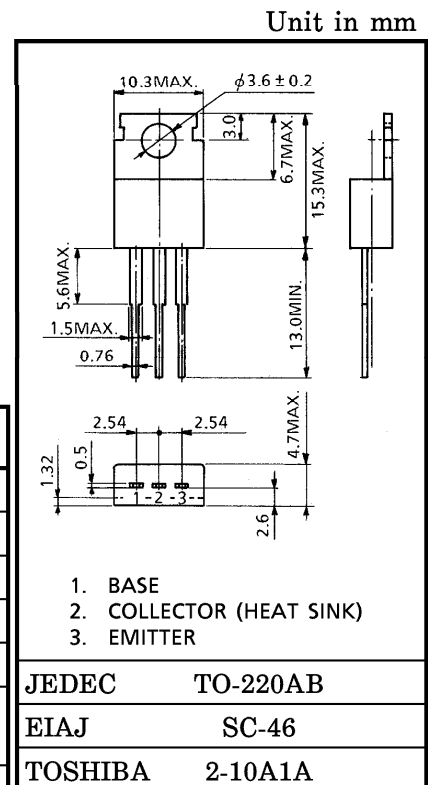
2SD526

POWER AMPLIFIER APPLICATIONS

- High Power Dissipation : $P_C = 30\text{W}$ ($T_c = 25^\circ\text{C}$)
- Good Linearity of h_{FE} .
- Complementary to 2SB596.
- Recommend for 20~25W High Fidelity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	4	A
Base Current	I_B	0.4	A
Collector Power Dissipation ($T_c = 25^\circ\text{C}$)	P_C	30	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$



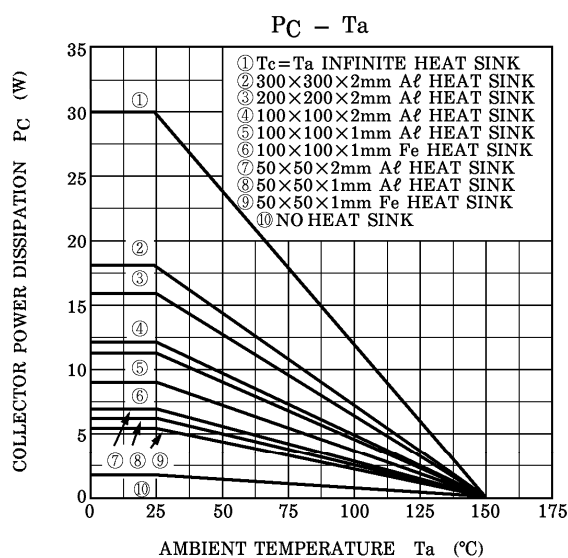
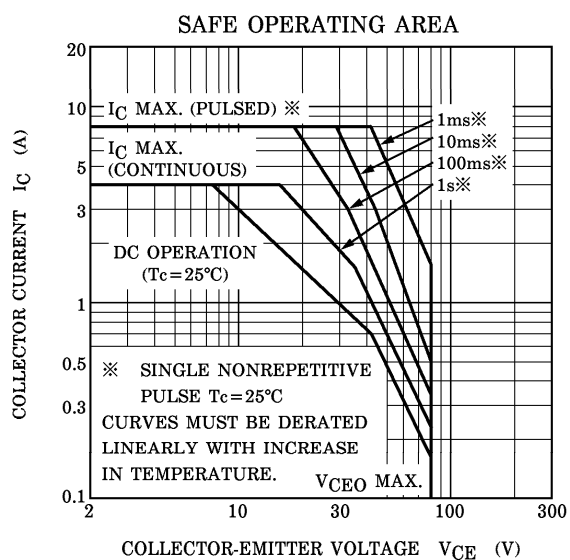
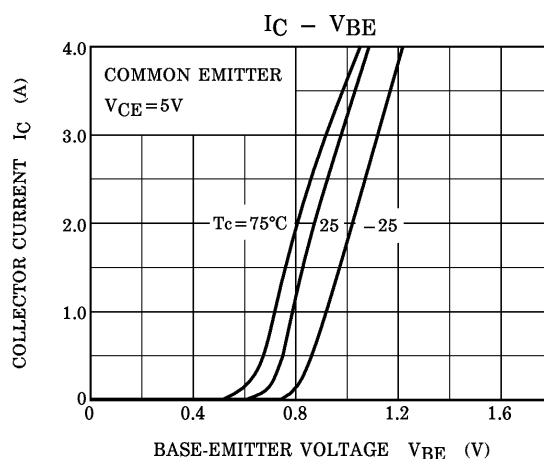
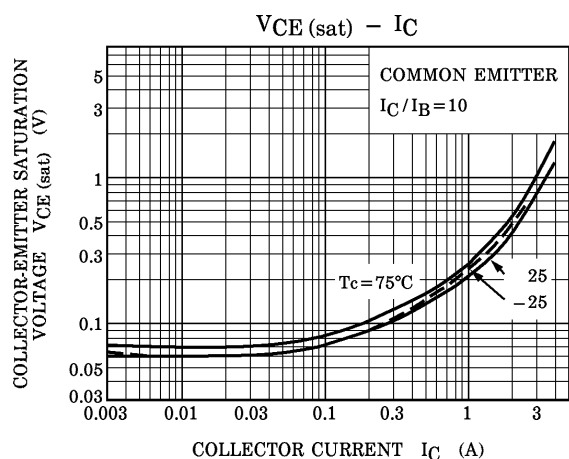
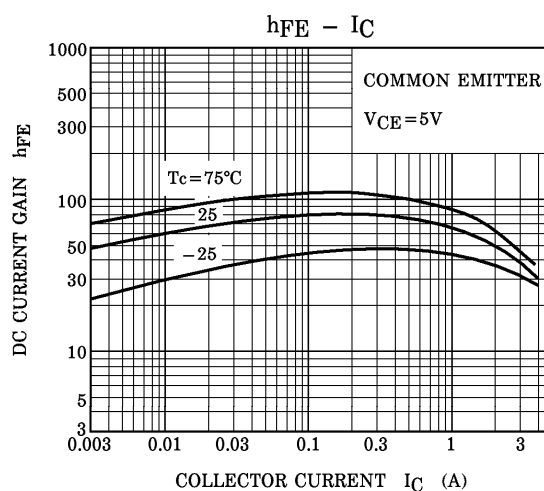
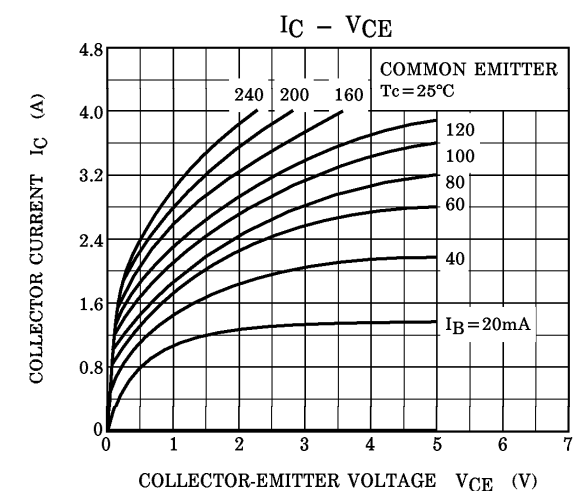
Weight : 1.9g

Mounting Kit No. AC75

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 80\text{V}$, $I_E = 0$	—	—	30	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 5\text{V}$, $I_C = 0$	—	—	100	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 50\text{mA}$, $I_B = 0$	80	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = 5\text{V}$, $I_C = 0.5\text{A}$	40	—	240	
	$h_{FE(2)}$	$V_{CE} = 5\text{V}$, $I_C = 3\text{A}$	15	50	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 3\text{A}$, $I_B = 0.3\text{A}$	—	0.45	1.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = 5\text{V}$, $I_C = 3\text{A}$	—	1.0	1.5	V
Transition Frequency	f_T	$V_{CE} = 5\text{V}$, $I_C = 0.5\text{A}$	3	8	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$	—	90	—	pF

Note : $h_{FE(1)}$ Classification R : 40~80, O : 70~140, Y : 120~240



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